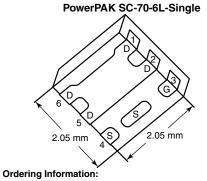


Vishay Siliconix

P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω) (Max.)	I _D (A)	Q _g (Typ.)			
- 30	0.021at V _{GS} = - 10 V	- 12 ^a	21 nC			
	0.030 at V _{GS} = - 4.5 V	- 12 ^a	21110			



SiA483DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

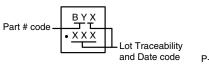
FEATURES

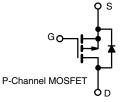
- TrenchFET[®] Power MOSFET
- Thermally Enhanced PowerPAK[®] SC-70 Package - Small Footprint Area
- Low On-Resistance
- 100 % R_g Tested
- Material categorization:
- For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Smart Phones, Tablet PCs, Mobile Computing:
 - Battery Switches
 - Load Switches
 - Power Management
 - DC/DC Converters







RoHS

COMPLIANT

HALOGEN

FREE

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 30	V	
Gate-Source Voltage		V _{GS}	± 20		
	T _C = 25 °C		- 12 ^a		
Continuous Drain Current (T 150 °C)	T _C = 70 °C		- 12 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	- 10 ^{b, c}		
	T _A = 70 °C		- 8 ^{b, c}	A	
Pulsed Drain Current (t = 300 μs)		I _{DM}	- 40	_	
Continuous Source-Drain Diode Current	T _C = 25 °C	1	- 12 ^a		
	T _A = 25 °C	I _S	- 2.9 ^{b, c}		
	T _C = 25 °C		19	1	
Maximum Power Dissipation	T _C = 70 °C		12	14/	
	T _A = 25 °C	P _D	3.5 ^{b, c}	W	
	T _A = 70 °C		2.2 ^{b, c}		
Operating Junction and Storage Temperature R	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	$t \le 5 s$	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	C/W	

Notes:

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

Rework conditions: manual soldering with a soldering iron is not recommended for leadless components. e.

Maximum under steady state conditions is 80 °C/W. f.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•	•		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA	- 30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L 050 ··· A		- 21		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μΑ		4.6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1		- 2.2	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	— μΑ	
		V_{DS} = - 30 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}					Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V, I _D = - 5 A		0.016	0.021	Ω	
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3 A		0.024	0.030		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 5 A		23		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1550			
Output Capacitance	C _{oss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		175		pF	
Reverse Transfer Capacitance	C _{rss}			150			
T		V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 10 A		29	45	nC	
Total Gate Charge				14	21		
Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_{D} = - 10 A		4.4			
Gate-Drain Charge	Q _{gd}			4.8			
Gate Resistance	R _g	f = 1 MHz	0.7	3.7	7.4	Ω	
Turn-On Delay Time	t _{d(on)}			37	80	ns	
Rise Time	t _r	V _{DD} = - 15 V, R _I = 1.9 Ω		30	60		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -8$ Å, $V_{GEN} = -4.5$ V, $R_g = 1$ Ω		25	50		
Fall Time	t _f			8	20		
Turn-On Delay Time	t _{d(on)}			10	10		
Rise Time	t _r	V_{DD} = - 15 V, R _L = 1.9 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -8$ Å, $V_{GEN} = -10$ V, $R_g = 1$ Ω		27	55		
Fall Time	t _f			9	20		
Drain-Source Body Diode Characterist	ics			•	•		
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			- 12		
Pulse Diode Forward Current	I _{SM}				- 40	A	
Body Diode Voltage	V _{SD}	I _S = - 8 A, V _{GS} = 0		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			17	40	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			10	20	nC	
Reverse Recovery Fall Time	t _a	I _F = - 8 A, dl/dt = 100 A/μs, T _J = 25 °C		10		ns	
Reverse Recovery Rise Time	t _b			7			

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

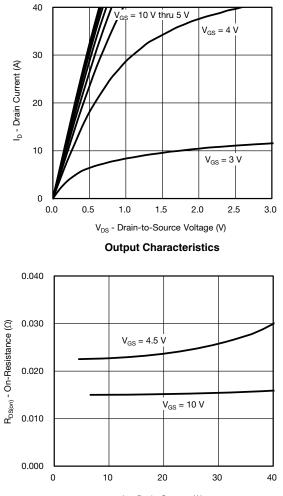
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Document Number: 62779 S12-2394-Rev. A, 15-Oct-12



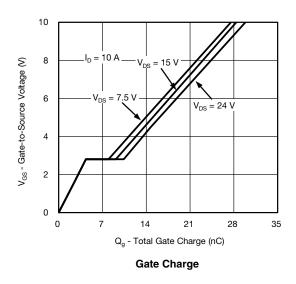
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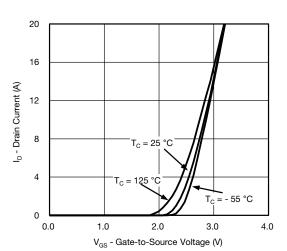
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



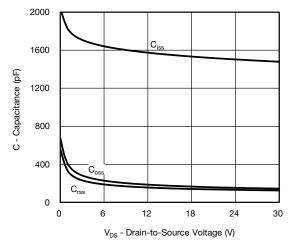
I_D - Drain Current (A)

On-Resistance vs. Drain Current and Gate Voltage

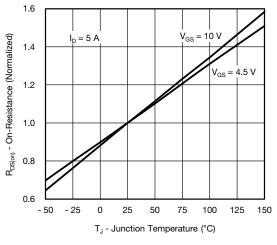




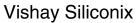
Transfer Characteristics



Capacitance

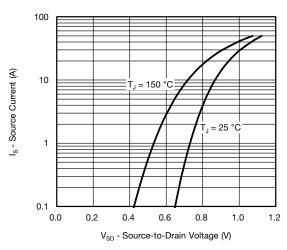


On-Resistance vs. Junction Temperature

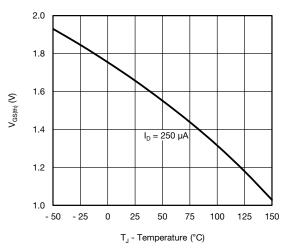




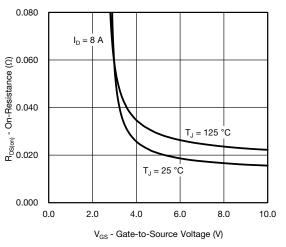
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



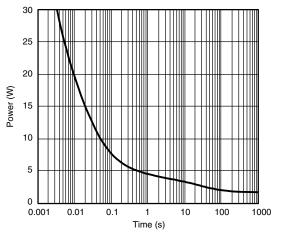
Soure-Drain Diode Forward Voltage



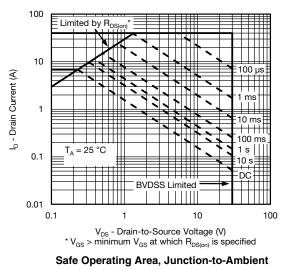
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



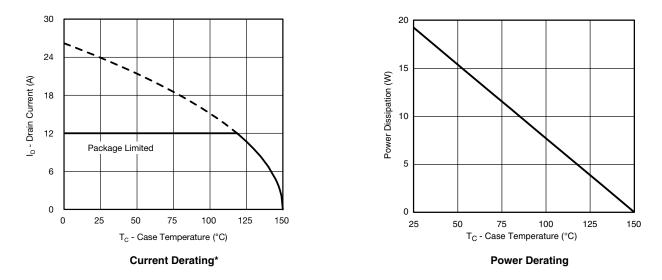
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New Product

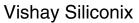


SiA483DJ Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

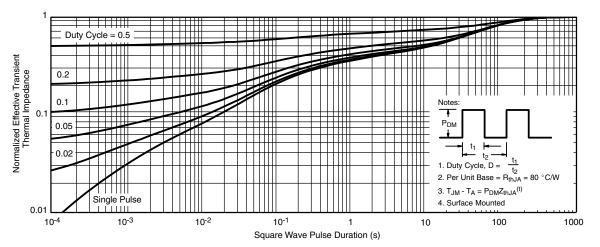


* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

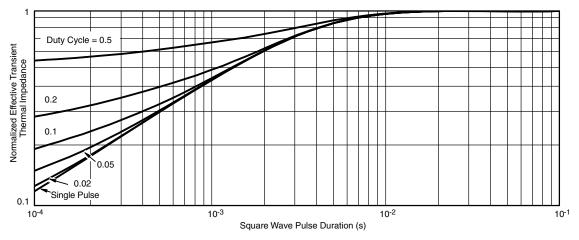




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

¥

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¹



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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Vishay

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